



<IGBT Modules>

CM100MXUD-13T1/CM100MXUDP-13T1

**HIGH POWER SWITCHING USE
INSULATED TYPE**

 <p>MXUD</p>	<p>Collector current I_c 1 0 0 A Collector-emitter voltage V_{CES} 6 5 0 V Maximum junction temperature T_{vjmax} 1 7 5 °C</p> <ul style="list-style-type: none"> •Flat base type •Copper base plate (Nickel-plating) •RoHS Directive compliant •Tin-plating pin terminals
 <p>MXUDP</p>	<p>Collector current I_c 1 0 0 A Collector-emitter voltage V_{CES} 6 5 0 V Maximum junction temperature T_{vjmax} 1 7 5 °C</p> <ul style="list-style-type: none"> •Flat base type •Copper base plate (Nickel-plating) •RoHS Directive compliant •Tin-plating pressfit terminals <p>•UL Recognized under UL1557, File No. E323585</p>

CIB (Converter+Inverter+Chopper Brake)

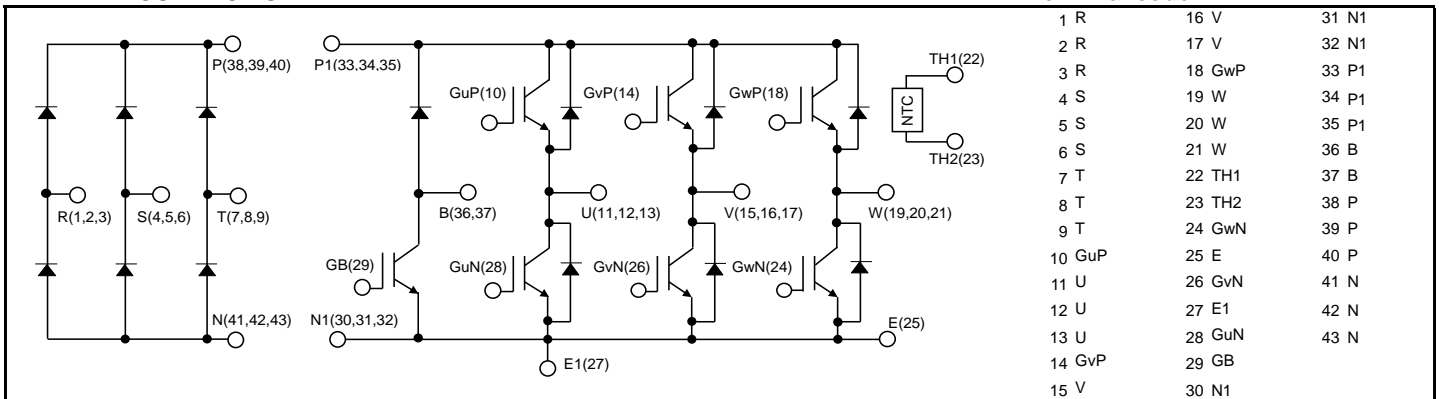
APPLICATION

AC Motor Control, Motion/Servo Control, Power supply, etc.

OPTION (Below options are available.)

- PC-TIM (Phase Change Thermal Interface Material) pre-apply

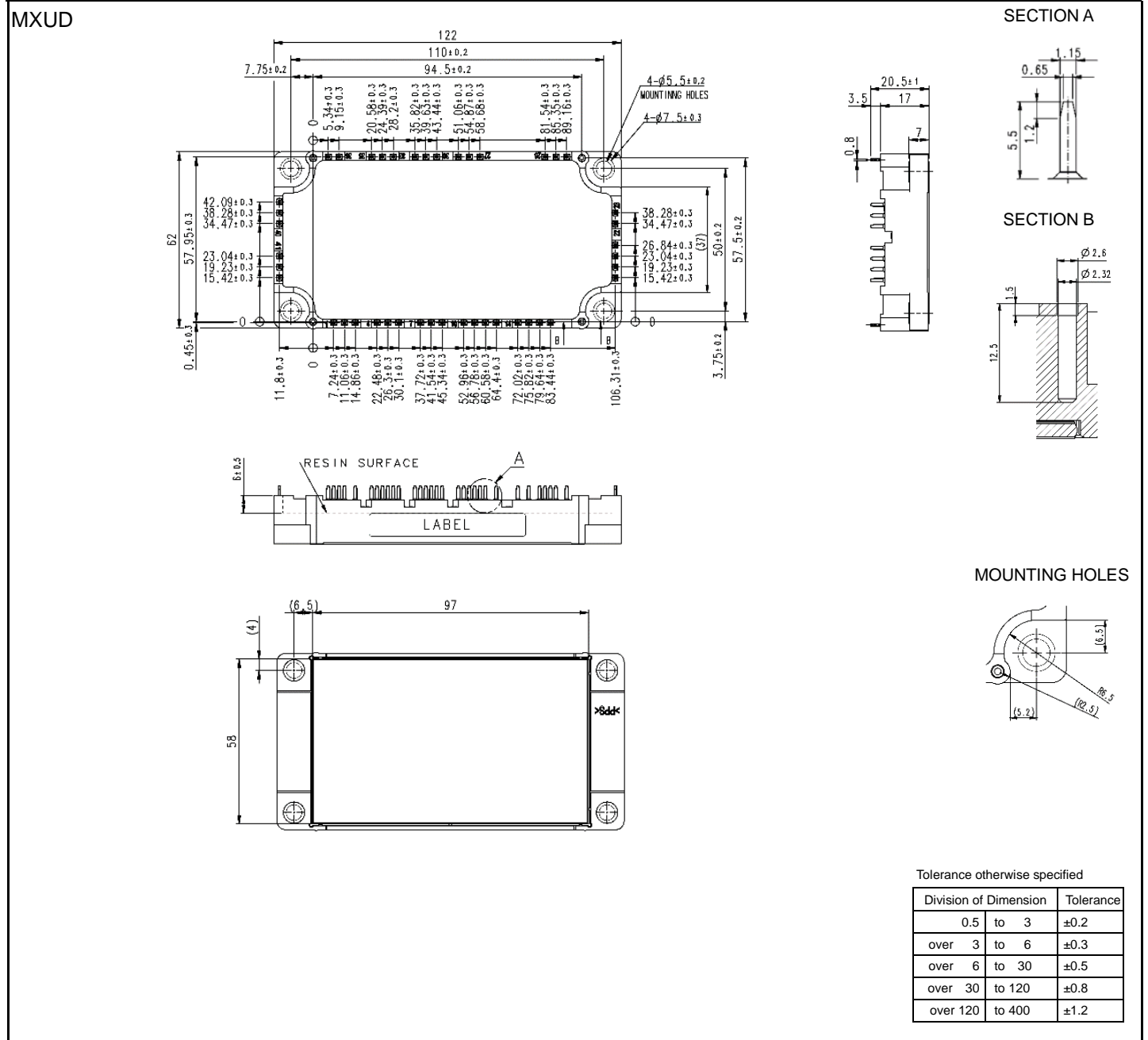
INTERNAL CONNECTION



CM100MXUD-13T1/CM100MXUDP-13T1

HIGH POWER SWITCHING USE
INSULATED TYPE

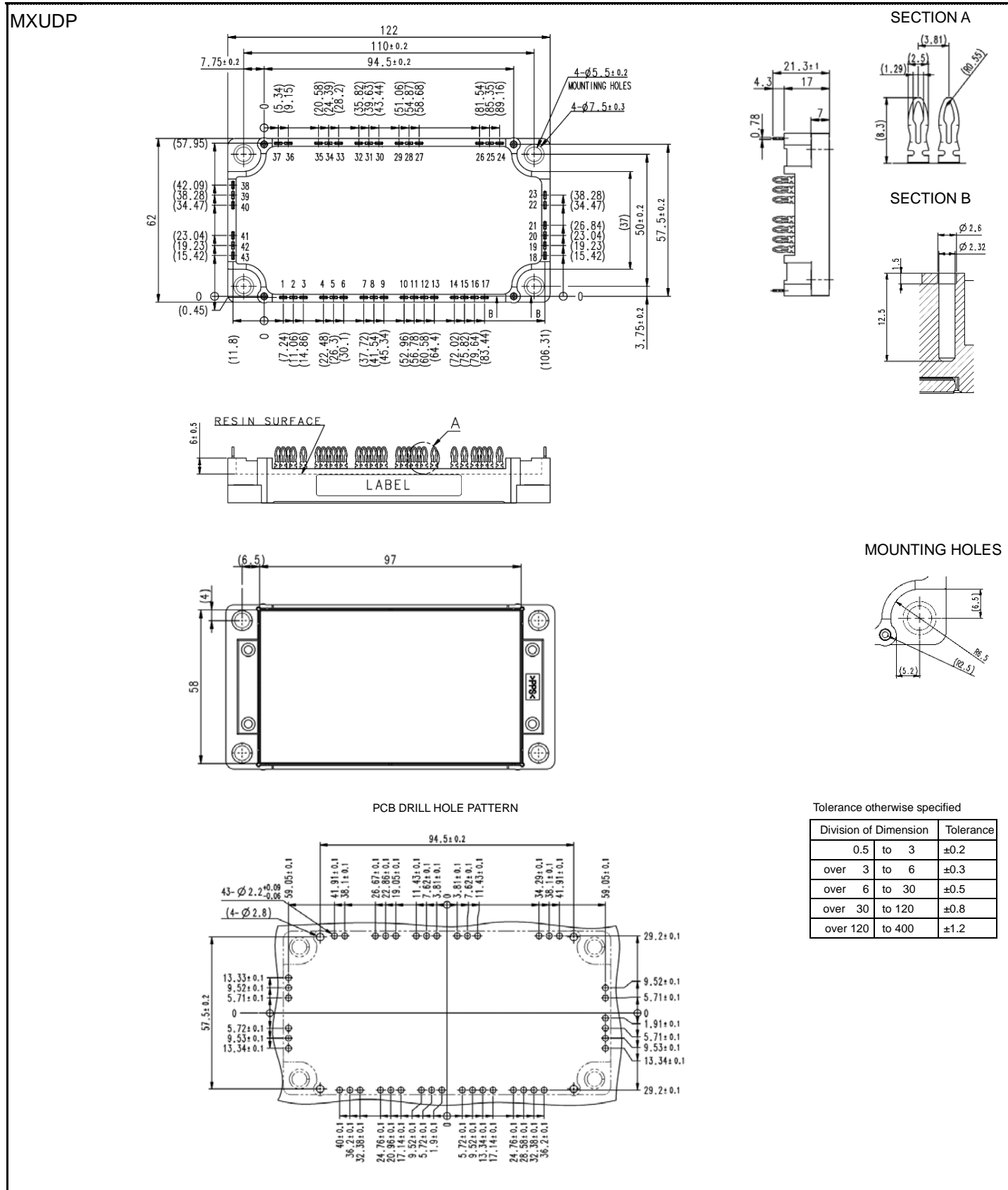
OUTLINE DRAWING



CM100MXUD-13T1/CM100MXUDP-13T1

HIGH POWER SWITCHING USE
INSULATED TYPE

OUTLINE DRAWING



CM100MXUD-13T1/CM100MXUDP-13T1

HIGH POWER SWITCHING USE
INSULATED TYPE**MAXIMUM RATINGS (T_{vj}=25 °C, unless otherwise specified)****INVERTER PART IGBT/FWD**

Symbol	Item	Conditions	Rating	Unit
V _{CES}	Collector-emitter voltage	G-E short-circuited	650	V
V _{GES}	Gate-emitter voltage	C-E short-circuited	± 20	V
I _C	Collector current	DC, T _C =90°C (Note2, 4)	100	A
I _{CRM}		Pulse, Repetitive (Note3)	200	
P _{tot}	Total power dissipation	T _C =25 °C (Note2, 4)	325	W
I _E (Note1)	Emitter current	DC (Note2)	100	A
I _{ERM} (Note1)		Pulse, Repetitive (Note3)	200	
T _{vjmax}	Maximum junction temperature	Instantaneous event (overload)	175	°C

BRAKE PART IGBT/DIODE

Symbol	Item	Conditions	Rating	Unit
V _{CES}	Collector-emitter voltage	G-E short-circuited	650	V
V _{GES}	Gate-emitter voltage	C-E short-circuited	± 20	V
I _C	Collector current	DC, T _C =96 °C (Note2, 4)	75	A
I _{CRM}		Pulse, Repetitive (Note3)	150	
P _{tot}	Total power dissipation	T _C =25 °C (Note2, 4)	270	W
V _{RRM}	Repetitive peak reverse voltage	G-E short-circuited	650	V
I _F	Forward current	DC (Note2)	50	A
I _{FRM}		Pulse, Repetitive (Note3)	100	
T _{vjmax}	Maximum junction temperature	Instantaneous event (overload)	175	°C

CONVERTER PART DIODE

Symbol	Item	Conditions	Rating	Unit	
V _{RRM}	Repetitive peak reverse voltage	-	800	V	
E _a	Recommended AC input voltage	RMS	220	V	
I _o	DC output current	3-phase full wave rectifying, T _C =118 °C (Note4)	100	A	
I _{FSM}	Surge forward current	The sine half wave 1 cycle peak value, f=60 Hz, non-repetitive	T _{vj} =25 °C	900	A
			T _{vj} =150 °C	720	
I ² _t	Current square time	Value for one cycle of surge current	T _{vj} =25 °C	3375	A ² s
			T _{vj} =150 °C	2160	
T _{vjmax}	Maximum junction temperature	Instantaneous event (overload)	150	°C	

MODULE

Symbol	Item	Conditions	Rating	Unit
V _{isol}	Isolation voltage	Terminals to base plate, RMS, f=60 Hz, AC 1 min	2500	V
T _{Cmax}	Maximum case temperature	(Note4)	125	°C
T _{vjop}	Operating junction temperature	Continuous operation (under switching)	-40 ~ +150	°C
T _{stg}	Storage temperature	-	-40 ~ +125	

CM100MXUD-13T1/CM100MXUDP-13T1

HIGH POWER SWITCHING USE
INSULATED TYPE**ELECTRICAL CHARACTERISTICS (T_{vj}=25 °C, unless otherwise specified)**
INVERTER PART IGBT/FWD

Symbol	Item	Conditions	Limits			Unit	
			Min.	Typ.	Max.		
I _{CEs}	Collector-emitter cut-off current	V _{CE} =V _{CEs} , G-E short-circuited	-	-	1.0	mA	
I _{GES}	Gate-emitter leakage current	V _{GE} =V _{GES} , C-E short-circuited	-	-	0.5	μA	
V _{GE(th)}	Gate-emitter threshold voltage	I _C =10 mA, V _{CE} =10 V	5.4	6.0	6.6	V	
V _{CEsat} (Terminal)	Collector-emitter saturation voltage	I _C =100 A, V _{GE} =15 V, Refer to the figure of test circuit (Note5)	T _{vj} =25 °C	-	1.65	2.00	V
			T _{vj} =125 °C	-	1.95	-	
			T _{vj} =150 °C	-	2.05	-	
V _{CEsat} (Chip)	Collector-emitter saturation voltage	I _C =100 A, V _{GE} =15 V, (Note5)	T _{vj} =25 °C	-	1.45	1.70	V
			T _{vj} =125 °C	-	1.50	-	
			T _{vj} =150 °C	-	1.50	-	
C _{ies}	Input capacitance	V _{CE} =10 V, G-E short-circuited	-	-	10.1	nF	
C _{oes}	Output capacitance		-	-	0.5		
C _{res}	Reverse transfer capacitance		-	-	0.2		
Q _G	Gate charge	V _{CC} =300 V, I _C =100 A, V _{GE} =15 V	-	0.31	-	μC	
t _{d(on)}	Turn-on delay time	V _{CC} =300 V, I _C =100 A, V _{GE} =±15 V, R _G =6.8 Ω, Inductive load	-	-	400	ns	
t _r	Rise time		-	-	200		
t _{d(off)}	Turn-off delay time		-	-	400		
t _f	Fall time		-	-	600		
V _{EC} (Note1) (Terminal)	Emitter-collector voltage	I _E =100 A, G-E short-circuited, Refer to the figure of test circuit (Note5)	T _{vj} =25 °C	-	1.80	2.20	V
			T _{vj} =125 °C	-	2.00	-	
			T _{vj} =150 °C	-	2.05	-	
V _{EC} (Note1) (Chip)	Emitter-collector voltage	I _E =100 A, G-E short-circuited, (Note5)	T _{vj} =25 °C	-	1.45	1.85	V
			T _{vj} =125 °C	-	1.50	-	
			T _{vj} =150 °C	-	1.50	-	
t _{rr} (Note1)	Reverse recovery time	V _{CC} =300 V, I _E =100 A, V _{GE} =±15 V, R _G =6.8 Ω, Inductive load	-	-	400	ns	
Q _{rr} (Note1)	Reverse recovery charge	R _G =6.8 Ω, Inductive load	-	6.5	-	μC	
E _{on}	Turn-on switching energy per pulse	V _{CC} =300 V, I _C =I _E =100 A,	-	2.6	-	mJ	
E _{off}	Turn-off switching energy per pulse	V _{GE} =±15 V, R _G =6.8Ω, T _{vj} =150 °C, Inductive load	-	4.8	-		
E _{rr} (Note1)	Reverse recovery energy per pulse	Inductive load	-	5.3	-	mJ	
r _g	Internal gate resistance	Per switch	-	0	-	Ω	

BRAKE PART IGBT/DIODE

Symbol	Item	Conditions	Limits			Unit	
			Min.	Typ.	Max.		
I _{CEs}	Collector-emitter cut-off current	V _{CE} =V _{CEs} , G-E short-circuited	-	-	1.0	mA	
I _{GES}	Gate-emitter leakage current	V _{GE} =V _{GES} , C-E short-circuited	-	-	0.5	μA	
V _{GE(th)}	Gate-emitter threshold voltage	I _C =7.5 mA, V _{CE} =10 V	5.4	6.0	6.6	V	
V _{CEsat} (Terminal)	Collector-emitter saturation voltage	I _C =75 A, V _{GE} =15 V, Refer to the figure of test circuit (Note5)	T _{vj} =25 °C	-	1.65	2.10	V
			T _{vj} =125 °C	-	1.90	-	
			T _{vj} =150 °C	-	2.00	-	
V _{CEsat} (Chip)	Collector-emitter saturation voltage	I _C =75 A, V _{GE} =15 V, (Note5)	T _{vj} =25 °C	-	1.50	1.75	V
			T _{vj} =125 °C	-	1.55	-	
			T _{vj} =150 °C	-	1.55	-	
C _{ies}	Input capacitance	V _{CE} =10 V, G-E short-circuited	-	-	6.7	nF	
C _{oes}	Output capacitance		-	-	0.3		
C _{res}	Reverse transfer capacitance		-	-	0.1		
Q _G	Gate charge	V _{CC} =300 V, I _C =75 A, V _{GE} =15 V	-	0.21	-	μC	
t _{d(on)}	Turn-on delay time	V _{CC} =300 V, I _C =75 A, V _{GE} =±15 V, R _G =10 Ω, Inductive load	-	-	400	ns	
t _r	Rise time		-	-	200		
t _{d(off)}	Turn-off delay time		-	-	400		
t _f	Fall time		-	-	600		

CM100MXUD-13T1/CM100MXUDP-13T1

HIGH POWER SWITCHING USE
INSULATED TYPEELECTRICAL CHARACTERISTICS (cont.; $T_{vj}=25\text{ }^{\circ}\text{C}$, unless otherwise specified)

BRAKE PART IGBT/DIODE

Symbol	Item	Conditions	Limits			Unit		
			Min.	Typ.	Max.			
E_{on}	Turn-on switching energy per pulse	$V_{CC}=300\text{ V}$, $V_{GE}=\pm 15\text{ V}$, $T_{vj}=150\text{ }^{\circ}\text{C}$, Inductive load	$I_C=75\text{ A}$, $R_G=10\text{ }\Omega$	-	1.4	-	mJ	
E_{off}	Turn-off switching energy per pulse			-	3.1	-		
E_{rr}	Reverse recovery energy per pulse			$I_E=75\text{ A}$, $R_G=10\text{ }\Omega$	-	3.2		-
r_g	Internal gate resistance	-	-	0	-	Ω		
I_{RRM}	Reverse current	$V_R=V_{RRM}$, G-E short-circuited	-	-	1.0	mA		
V_F (Terminal)	Forward voltage	$I_F=50\text{ A}$, G-E short-circuited, Refer to the figure of test circuit (Note5)		$T_{vj}=25\text{ }^{\circ}\text{C}$	-	1.70	2.30	V
				$T_{vj}=125\text{ }^{\circ}\text{C}$	-	1.80	-	
				$T_{vj}=150\text{ }^{\circ}\text{C}$	-	1.85	-	
V_F (Chip)	Forward voltage	$I_F=50\text{ A}$, G-E short-circuited, (Note5)		$T_{vj}=25\text{ }^{\circ}\text{C}$	-	1.45	1.85	V
				$T_{vj}=125\text{ }^{\circ}\text{C}$	-	1.50	-	
				$T_{vj}=150\text{ }^{\circ}\text{C}$	-	1.50	-	
t_{rr}	Reverse recovery time	$V_{CC}=300\text{ V}$, $I_F=50\text{ A}$, $V_{GE}=\pm 15\text{ V}$,	-	-	400	ns		
Q_{rr}	Reverse recovery charge	$R_G=15\text{ }\Omega$, Inductive load	-	5.0	-	μC		

CONVERTER PART DIODE

Symbol	Item	Conditions	Limits			Unit		
			Min.	Typ.	Max.			
I_{RRM}	Repetitive peak reverse current	$V_R=V_{RRM}$, $T_{vj}=150\text{ }^{\circ}\text{C}$	-	-	20	mA		
V_F (Terminal)	Forward voltage	$I_F=100\text{ A}$		$T_{vj}=25\text{ }^{\circ}\text{C}$	-	1.35	1.80	V
				$T_{vj}=150\text{ }^{\circ}\text{C}$	-	1.30	-	
V_F (chip)				$T_{vj}=25\text{ }^{\circ}\text{C}$	-	1.20	1.45	
				$T_{vj}=150\text{ }^{\circ}\text{C}$	-	1.15	-	

NTC THERMISTOR PART

Symbol	Item	Conditions	Limits			Unit
			Min.	Typ.	Max.	
R_{25}	Zero-power resistance	$T_C=25\text{ }^{\circ}\text{C}$ (Note4)	4.85	5.00	5.15	k Ω
$\Delta R/R$	Deviation of resistance	$R_{100}=493\text{ }\Omega$, $T_C=100\text{ }^{\circ}\text{C}$ (Note4)	-7.3	-	+7.8	%
$B_{(25/50)}$	B-constant	Approximate by equation (Note6)	-	3375	-	K
P_{25}	Power dissipation	$T_C=25\text{ }^{\circ}\text{C}$ (Note4)	-	-	10	mW

THERMAL RESISTANCE CHARACTERISTICS

Symbol	Item	Conditions	Limits			Unit	
			Min.	Typ.	Max.		
$R_{th(j-c)Q}$	Thermal resistance	Junction to case, per Inverter IGBT (Note4)	-	-	458	K/kW	
$R_{th(j-c)D}$		Junction to case, per Inverter FWD (Note4)	-	-	594		
$R_{th(j-c)Q}$		Junction to case, Brake IGBT (Note4)	-	-	554		
$R_{th(j-c)D}$		Junction to case, Brake DIODE (Note4)	-	-	1346		
$R_{th(j-c)D}$		Junction to case, per Converter DIODE (Note4)	-	-	650		
$R_{th(c-s)}$	Contact thermal resistance	Case to heat sink, per 1 module,	Thermal grease applied (Note4, 7)	-	11.5	-	K/kW
			PC-TIM applied (Note4, 8)	-	3.1	-	

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HIGH POWER SWITCHING USE
INSULATED TYPE

MECHANICAL CHARACTERISTICS

Symbol	Item	Conditions	Limits			Unit	
			Min.	Typ.	Max.		
M _s	Mounting torque	Mounting to heat sink M 5 screw	2.5	3.0	3.5	N·m	
d _s	Creepage distance	Solder pin type(MXUD)	Terminal to terminal	11.7	-	-	mm
			Terminal to base plate	18.3	-	-	
		Pressfit pin type(MXUDP)	Terminal to terminal	5.1	-	-	
			Terminal to base plate	15.8	-	-	
d _a	Clearance	Solder pin type(MXUD)	Terminal to terminal	6.5	-	-	
			Terminal to base plate	18.1	-	-	
		Pressfit pin type(MXUDP)	Terminal to terminal	5.0	-	-	
			Terminal to base plate	15.8	-	-	
e _c	Flatness of base plate	On the centerline X, Y (Note9)	±0	-	+200	µm	
m	mass	-	-	270	-	g	

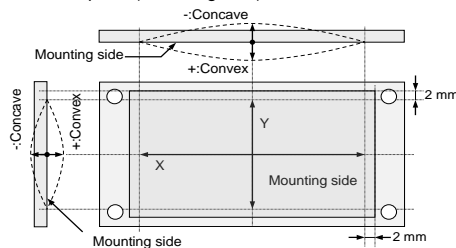
RECOMMENDED OPERATING CONDITIONS

Symbol	Item	Conditions	Limits			Unit
			Min.	Typ.	Max.	
V _{CC}	(DC) Supply voltage	Applied across P-N(P1-N1) terminals	-	300	450	V
V _{GEon}	Gate (-emitter drive) voltage	Applied across G*P-*/G*N-E/GB-E terminals (*=U,V,W) (Note11)	13.5	15.0	16.5	V
R _G	External gate resistance	Inverter IGBT, Per switch	6.8	-	68	Ω
		Brake IGBT	10	-	100	

*: This product is compliant with the Restriction of the Use of Certain Hazardous Substances in Electrical and Electronic Equipment (RoHS) directive 2011/65/EU.

Note1. Represent ratings and characteristics of the anti-parallel, emitter-collector free-wheeling diode (FWD).

- Junction temperature (T_{vj}) should not increase beyond T_{vjmax} rating.
- Pulse width and repetition rate should be such that the device junction temperature (T_{vj}) dose not exceed T_{vjmax} rating.
- Case temperature (T_C) and heat sink temperature (T_S) are defined on the each surface (mounting side) of base plate and heat sink just under the chips.
Refer to the figure of chip location.
- Pulse width and repetition rate should be such as to cause negligible temperature rise. Refer to the figure of test circuit.
- $B_{(25/50)} = \ln\left(\frac{R_{25}}{R_{50}}\right) / \left(\frac{1}{T_{25}} - \frac{1}{T_{50}}\right)$
R₂₅: resistance at absolute temperature T₂₅ [K]; T₂₅=25 [°C]+273.15=298.15 [K]
R₅₀: resistance at absolute temperature T₅₀ [K]; T₅₀=50 [°C]+273.15=323.15 [K]
- Typical value is measured by using thermally conductive grease of λ=0.9 W/(m·K)/D_(C-S)=50 µm.
- Typical value is measured by using PC-TIM of λ=3.4 W/(m·K)/D_(C-S)=50 µm.
- The base plate (mounting side) flatness measurement points (X, Y) are shown in the following figure.



- Use the following screws when mounting the printed circuit board (PCB) on the standoffs.

PCB thickness : t1.6

Type	Manufacturer	Size	Tightening torque (N·m)	Recommended tightening method
(1) PT®	EJOT	K25x8	0.55 ± 0.055	by handwork (equivalent to 30 rpm by mechanical screw driver) ~ 600 rpm (by mechanical screw driver)
(2) PT®		K25x10	0.75 ± 0.075 N·m	
(3) DELTA PT®		25x8	0.55 ± 0.055 N·m	
(4) DELTA PT®		25x10	0.75 ± 0.075 N·m	
(5) B1 tapping screw	-	φ2.6x10 φ2.6x12	0.75 ± 0.075 N·m	

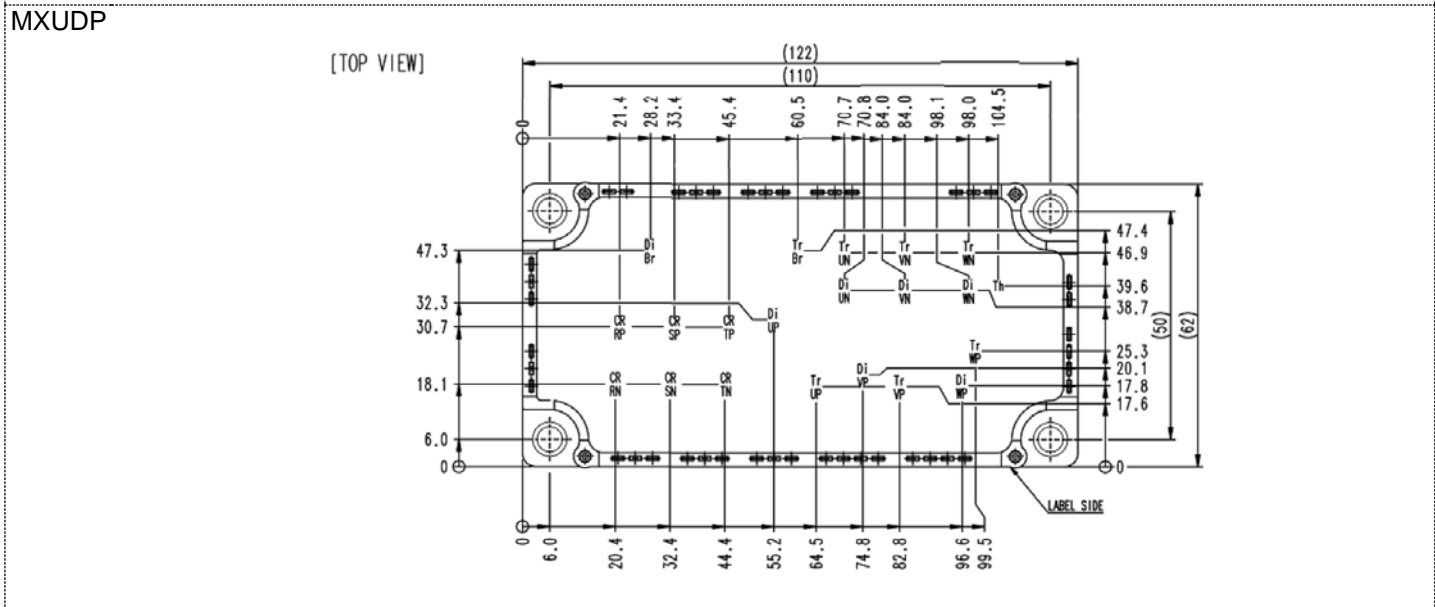
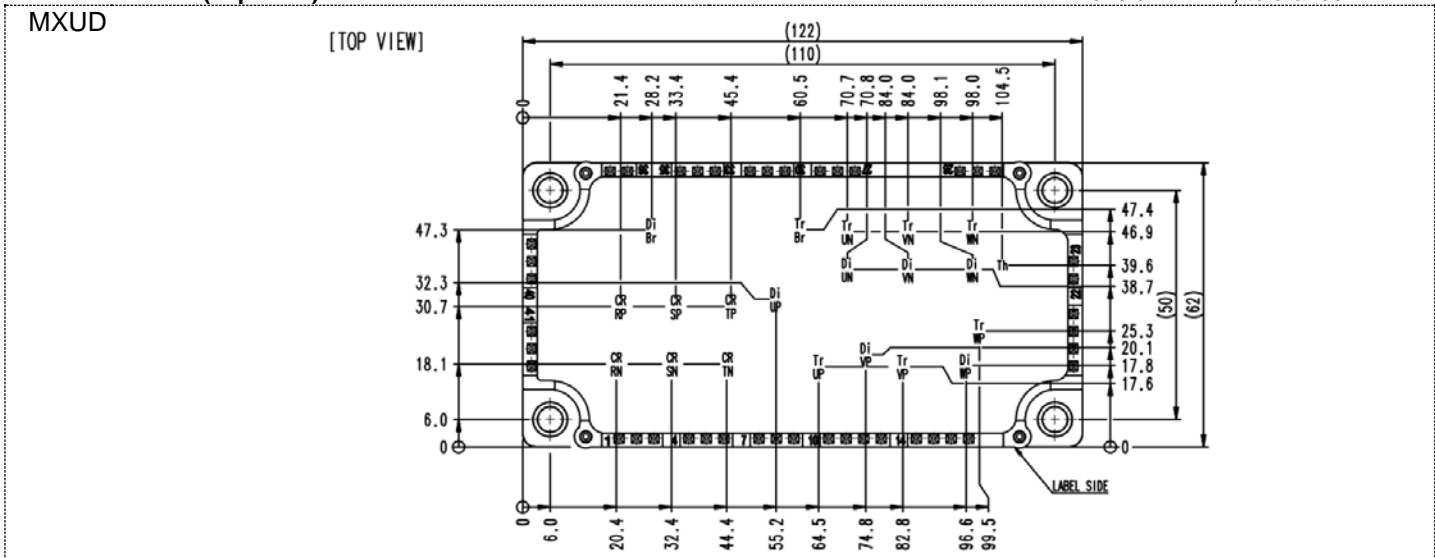
- V_{GEon}=15V is necessary for IGBT to operate at I_{CRM}.

CM100MXUD-13T1/CM100MXUDP-13T1

HIGH POWER SWITCHING USE
INSULATED TYPE

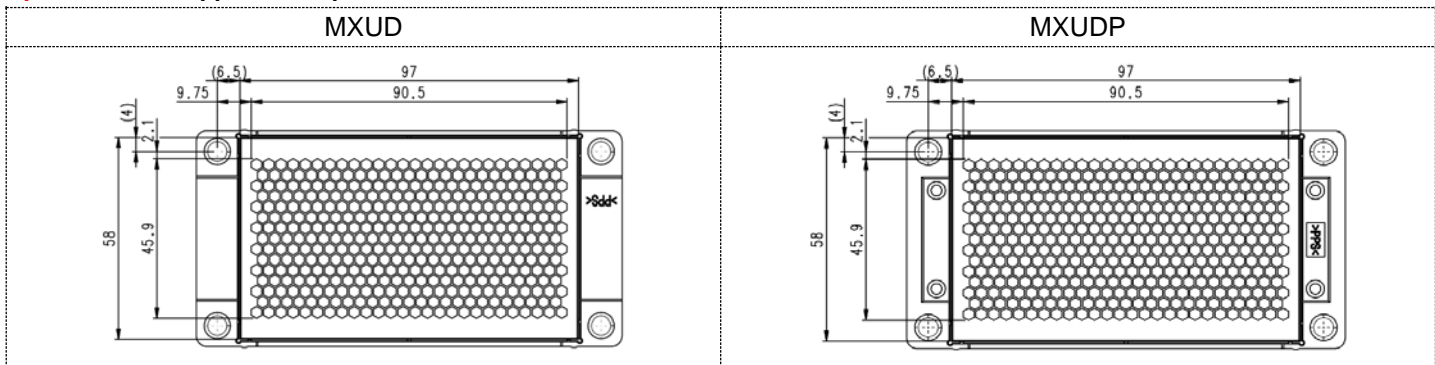
CHIP LOCATION (Top view)

Dimension in mm, tolerance: ±1 mm

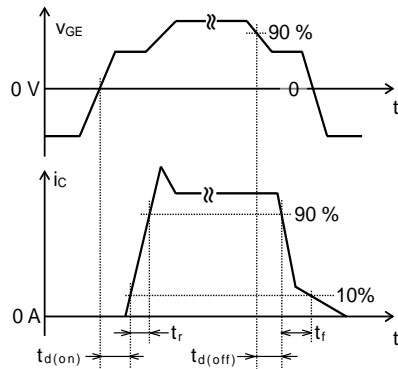
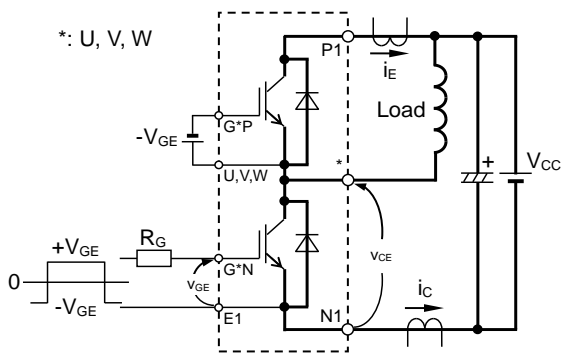


Tr*P/Tr*N/Tr*Br: IGBT, Di*P/Di*N: DIODE (*=U/V/W), DiBr: BRAKE DIODE,
CR*P/CR*N: CONVERTER DIODE (*=R/S/T), Th: NTC thermistor

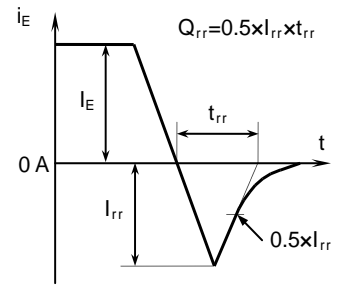
Option: PC-TIM applied baseplate outline



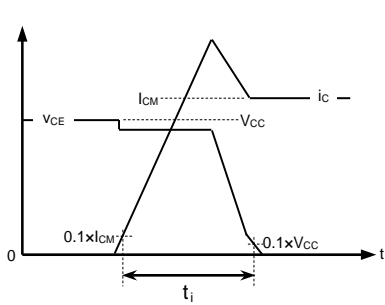
TEST CIRCUIT AND WAVEFORMS



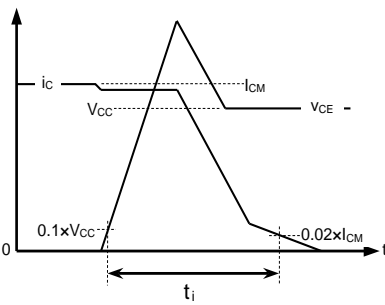
Switching characteristics test circuit and waveforms



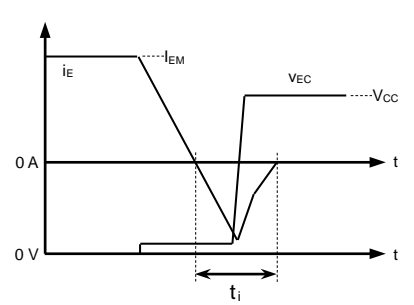
t_{rr} , Q_{rr} characteristics test waveform



IGBT Turn-on switching energy



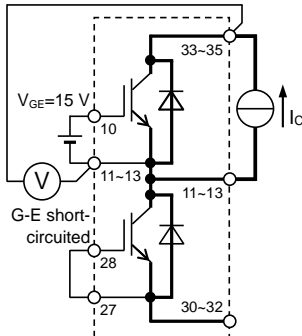
IGBT Turn-off switching energy



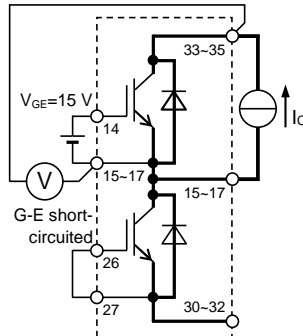
FWD Reverse recovery energy

Switching energy and Reverse recovery energy test waveforms (Integral time instruction drawing)

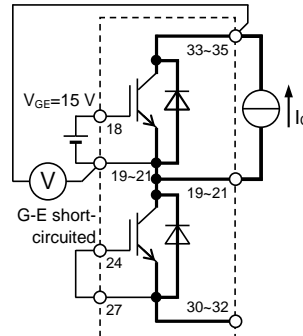
TEST CIRCUIT



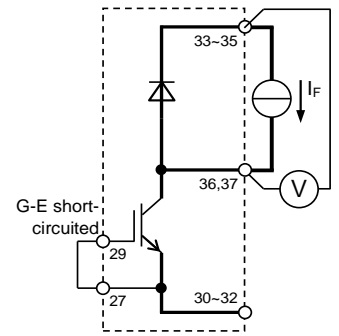
TrUP



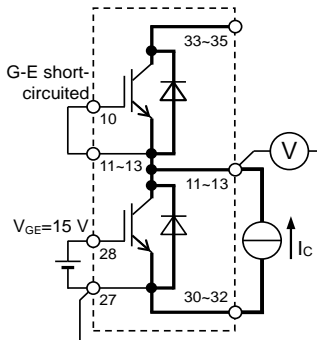
TrVP



TrWP

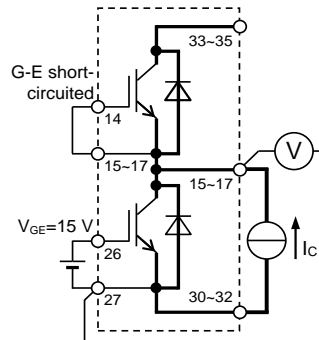


Brake DIODE



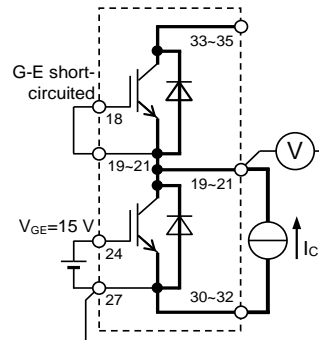
TrUN

Gate-emitter GVP-V, GVN-E1,
short-circuited GWP-W, GWN-E1
GB-E1



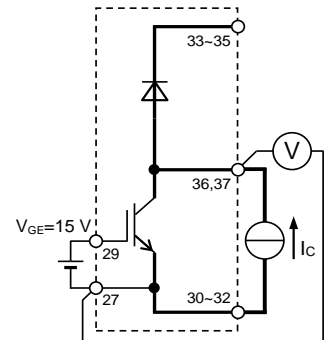
TrVN

Gate-emitter GUP-U, GUN-E1,
short-circuited GWP-W, GWN-E1
GB-E1



TrWN

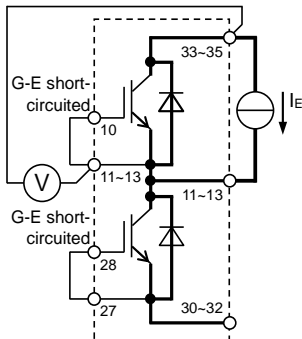
Gate-emitter GUP-U, GUN-E1,
short-circuited GVP-V, GVN-E1
GB-E1



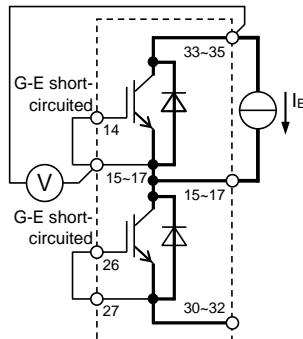
Brake IGBT

Gate-emitter GUP-U, GUN-E1,
short-circuited GVP-V, GVN-E1,
GWP-W, GWN-E1

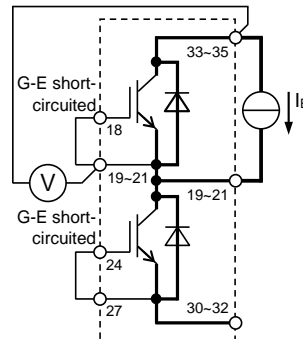
V_{CEsat} /BRAKE DIODE V_F characteristics test circuit



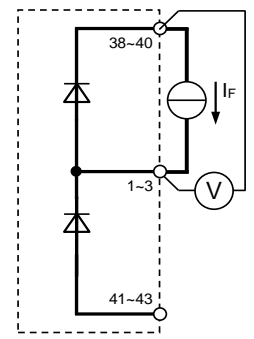
DiUP



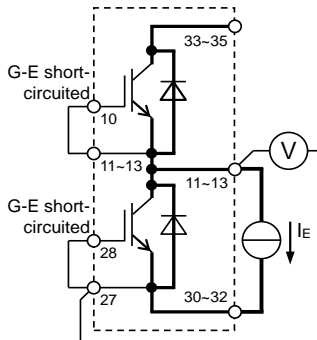
DiVP



DiWP

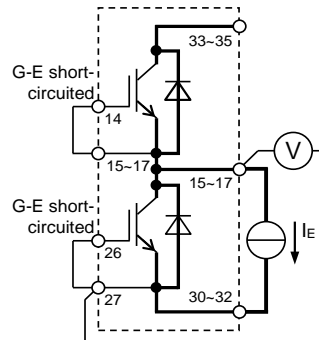


CONVERTER DIODE (ex.phase-R)



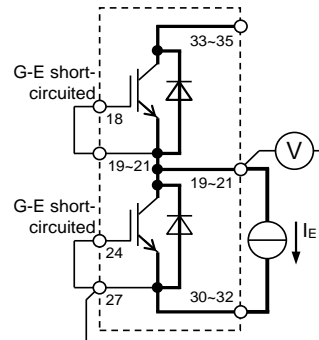
DiUN

Gate-emitter GVP-V, GVN-E1,
short-circuited GWP-W, GWN-E1
GB-E1



DiVN

Gate-emitter GUP-U, GUN-E1,
short-circuited GWP-W, GWN-E1
GB-E1



DiWN

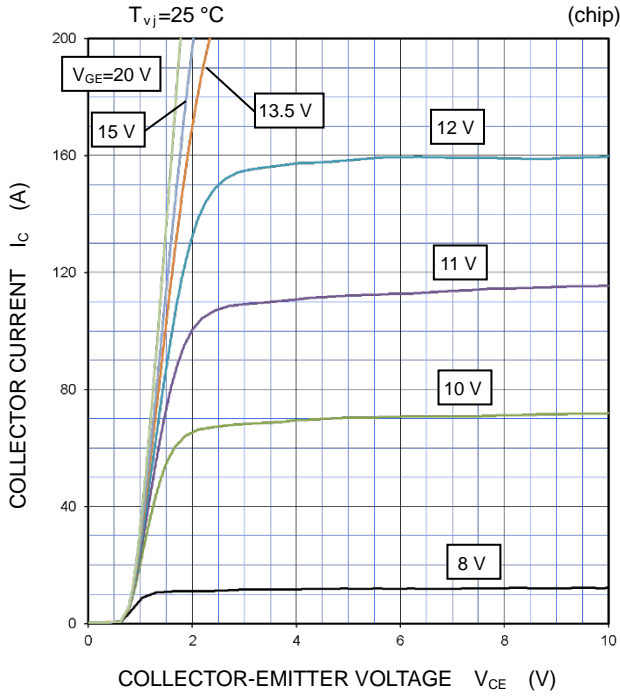
Gate-emitter GUP-U, GUN-E1,
short-circuited GVP-V, GVN-E1
GB-E1

V_{EC} / CONVERTER DIODE V_F characteristics test circuit

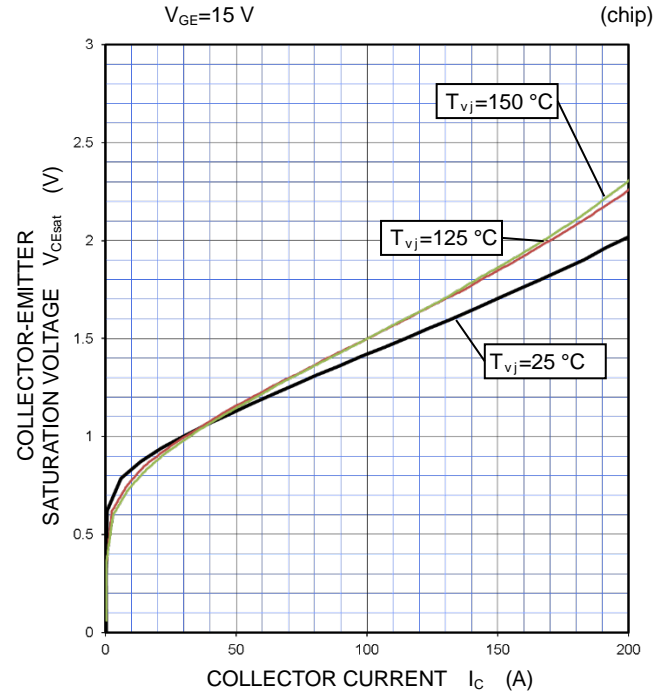
PERFORMANCE CURVES

INVERTER PART

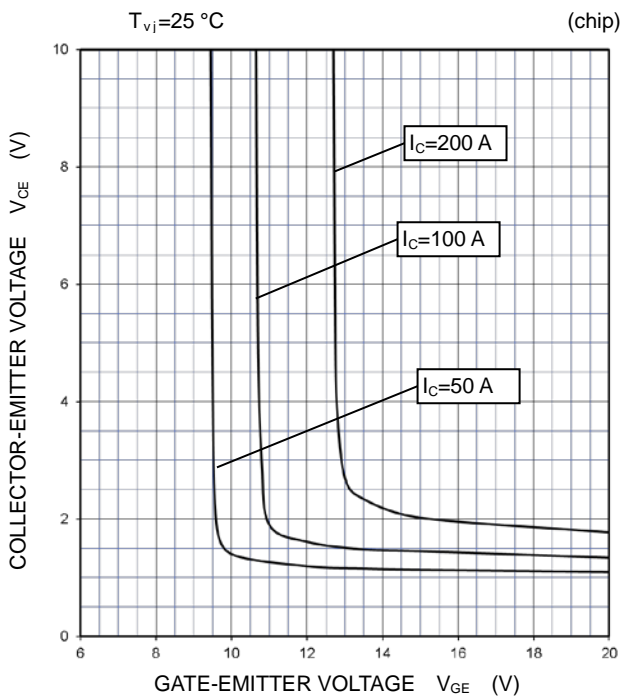
OUTPUT CHARACTERISTICS (TYPICAL)



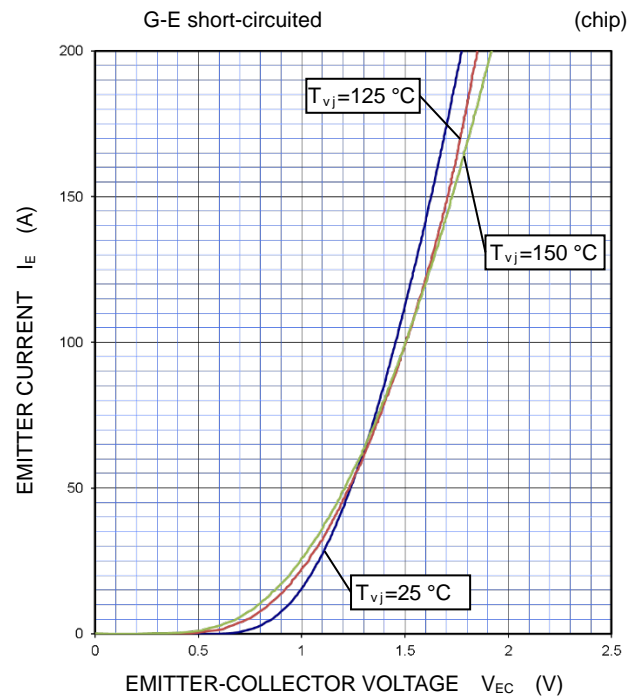
COLLECTOR-EMITTER SATURATION VOLTAGE CHARACTERISTICS (TYPICAL)



COLLECTOR-EMITTER VOLTAGE CHARACTERISTICS (TYPICAL)



FREE WHEELING DIODE FORWARD CHARACTERISTICS (TYPICAL)



CM100MXUD-13T1/CM100MXUDP-13T1

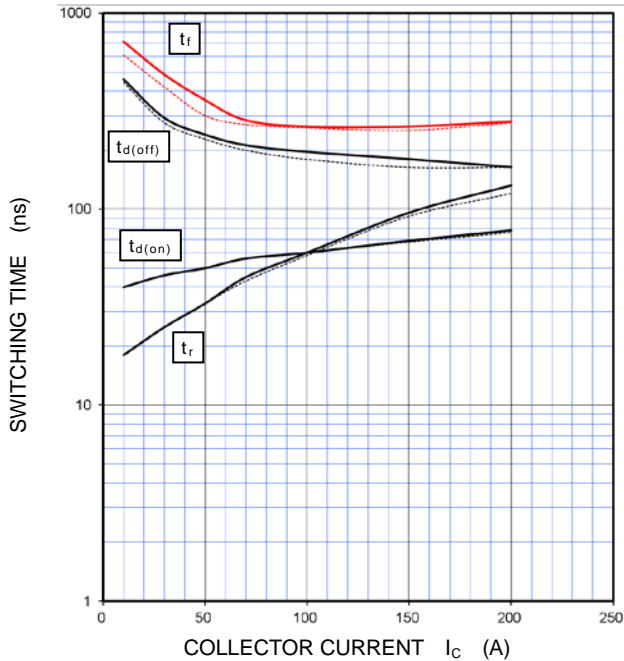
HIGH POWER SWITCHING USE
INSULATED TYPE

PERFORMANCE CURVES

INVERTER PART

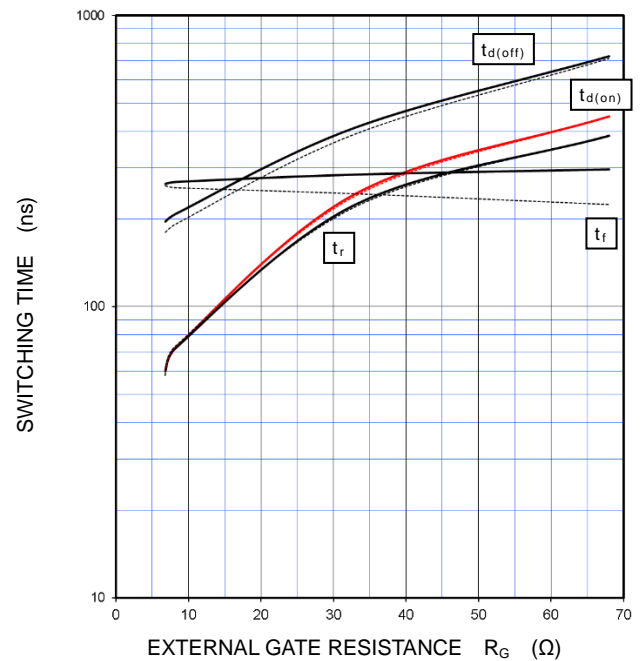
HALF-BRIDGE SWITCHING CHARACTERISTICS (TYPICAL)

$V_{CC}=300\text{ V}$, $R_G=6.8\ \Omega$, $V_{GE}=\pm 15\text{ V}$, INDUCTIVE LOAD
 —: $T_{vj}=150\text{ }^\circ\text{C}$, - - - -: $T_{vj}=125\text{ }^\circ\text{C}$



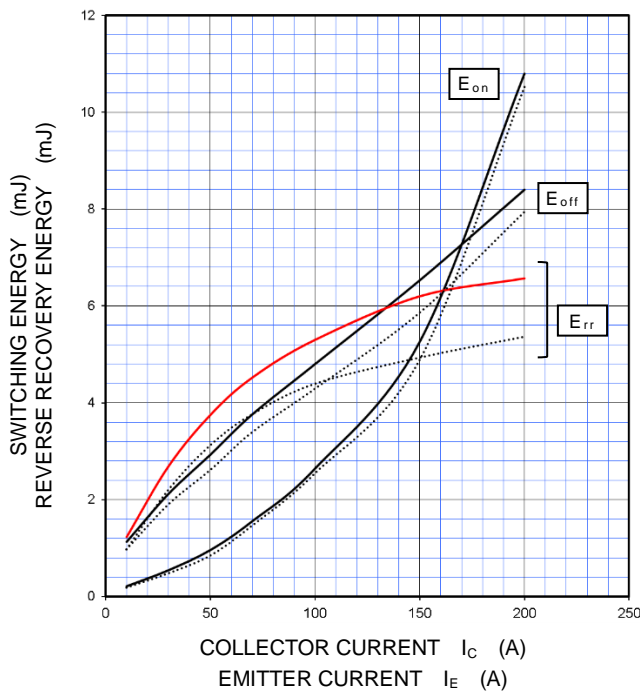
HALF-BRIDGE SWITCHING CHARACTERISTICS (TYPICAL)

$V_{CC}=300\text{ V}$, $I_C=100\text{ A}$, $V_{GE}=\pm 15\text{ V}$, INDUCTIVE LOAD
 —: $T_{vj}=150\text{ }^\circ\text{C}$, - - - -: $T_{vj}=125\text{ }^\circ\text{C}$



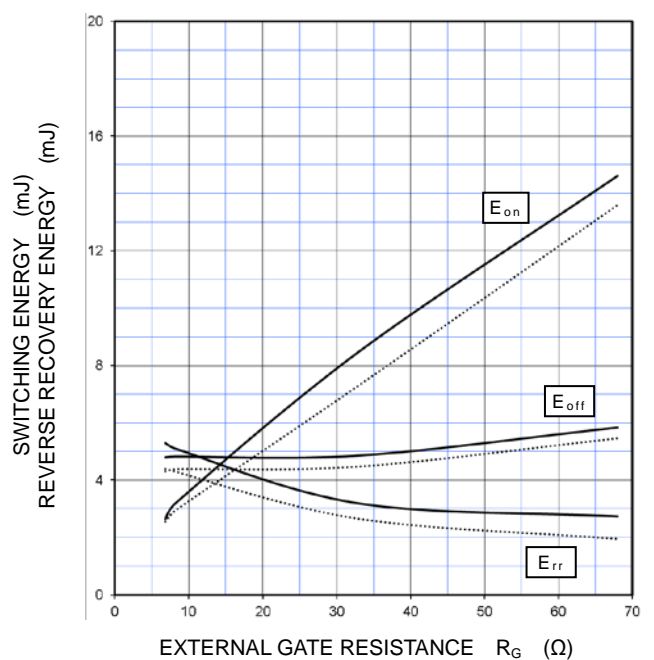
HALF-BRIDGE SWITCHING CHARACTERISTICS (TYPICAL)

$V_{CC}=300\text{ V}$, $R_G=6.8\ \Omega$, $V_{GE}=\pm 15\text{ V}$, INDUCTIVE LOAD,
 —: $T_{vj}=150\text{ }^\circ\text{C}$, - - - -: $T_{vj}=125\text{ }^\circ\text{C}$, PER PULSE



HALF-BRIDGE SWITCHING CHARACTERISTICS (TYPICAL)

$V_{CC}=300\text{ V}$, $I_C/I_E=100\text{ A}$, $V_{GE}=\pm 15\text{ V}$, INDUCTIVE LOAD,
 —: $T_{vj}=150\text{ }^\circ\text{C}$, - - - -: $T_{vj}=125\text{ }^\circ\text{C}$, PER PULSE



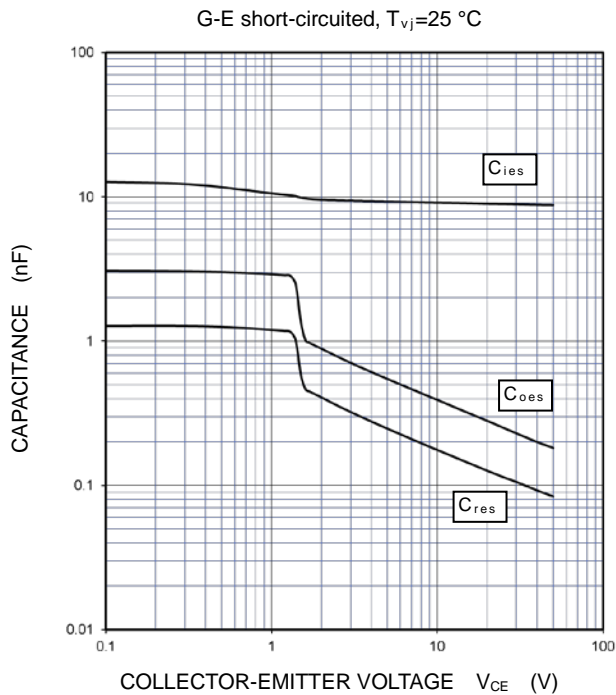
CM100MXUD-13T1/CM100MXUDP-13T1

HIGH POWER SWITCHING USE
INSULATED TYPE

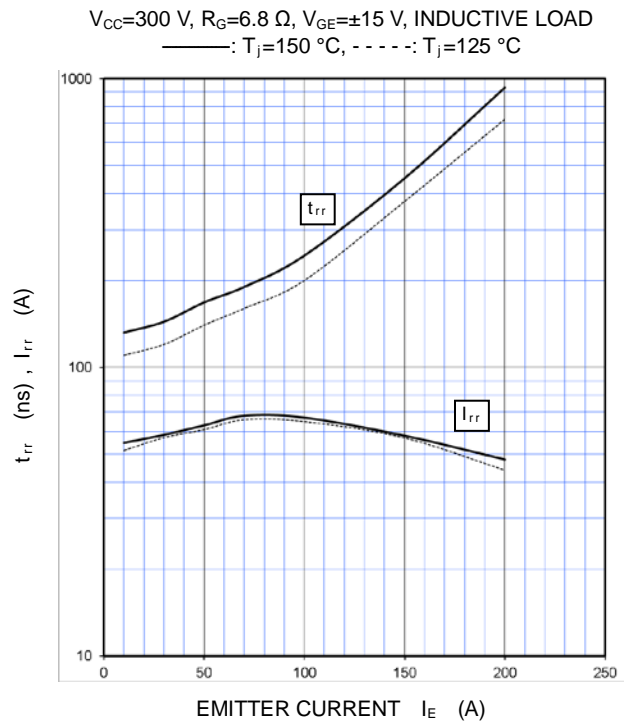
PERFORMANCE CURVES

INVERTER PART

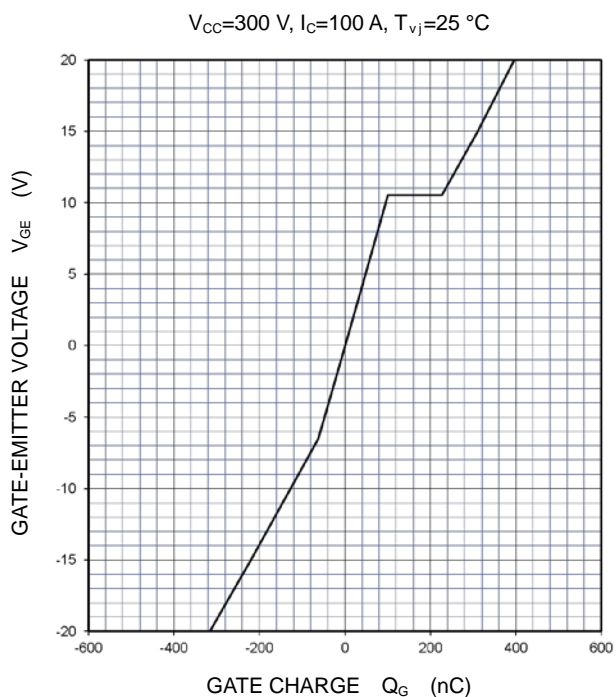
CAPACITANCE CHARACTERISTICS (TYPICAL)



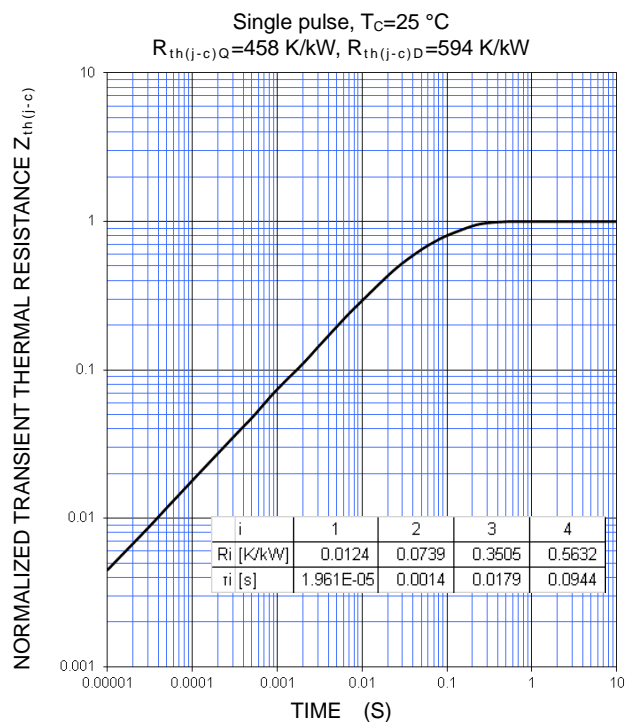
FREE WHEELING DIODE REVERSE RECOVERY CHARACTERISTICS (TYPICAL)



GATE CHARGE CHARACTERISTICS (TYPICAL)



TRANSIENT THERMAL IMPEDANCE CHARACTERISTICS (MAXIMUM)



CM100MXUD-13T1/CM100MXUDP-13T1

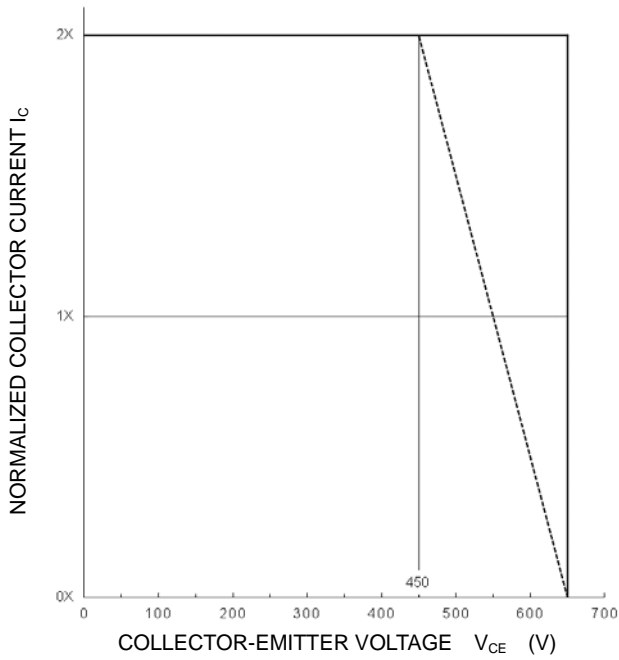
HIGH POWER SWITCHING USE
INSULATED TYPE

PERFORMANCE CURVES

INVERTER PART

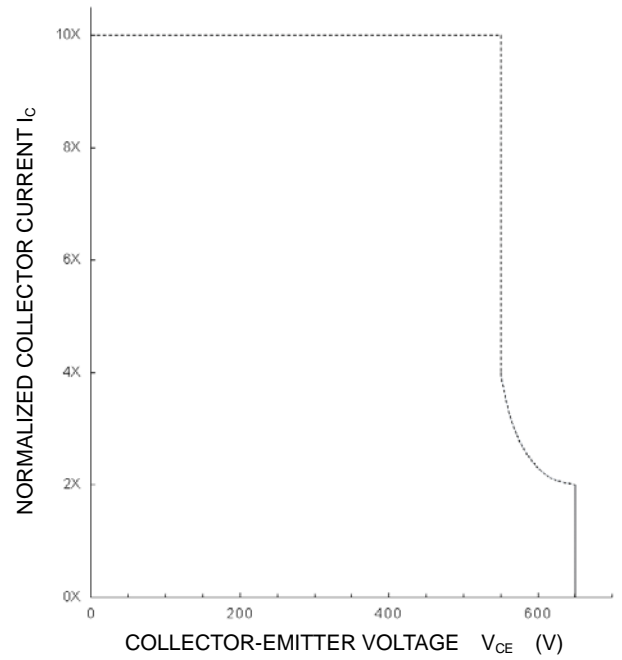
**TURN-OFF SWITCHING SAFE OPERATING AREA
(REVERSE BIAS SAFE OPERATING AREA)
(MAXIMUM)**

$V_{CC} \leq 450 \text{ V}$, $R_G = 6.8 \sim 68 \ \Omega$, $V_{GE} = \pm 15 \text{ V}$,
——: $T_{vj} = 25 \sim 150 \text{ }^\circ\text{C}$ (Normal load operations (Continuous))
- - - - -: $T_{vj} = 175 \text{ }^\circ\text{C}$ (Unusual load operations (Limited period))



**SHORT-CIRCUIT SAFE OPERATING AREA
(MAXIMUM)**

$V_{CC} \leq 400 \text{ V}$, $R_G = 6.8 \sim 68 \ \Omega$, $V_{GE} = \pm 15 \text{ V}$,
 $T_{vj} = 25 \sim 150 \text{ }^\circ\text{C}$, $t_W \leq 8 \ \mu\text{s}$, Non-Repetitive



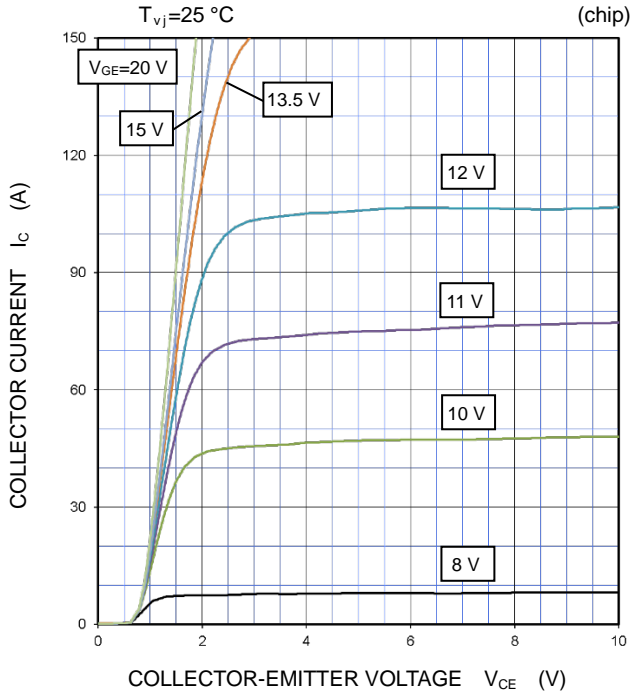
CM100MXUD-13T1/CM100MXUDP-13T1

HIGH POWER SWITCHING USE
INSULATED TYPE

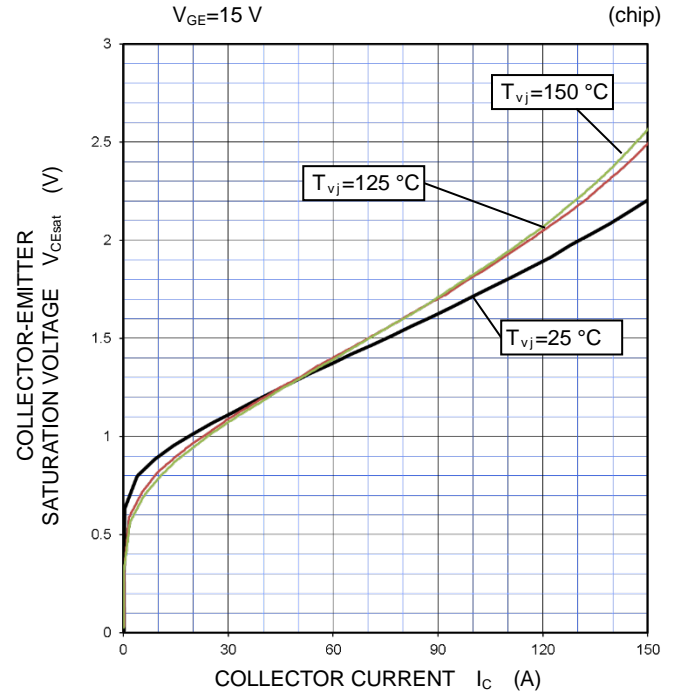
PERFORMANCE CURVES

BRAKE PART

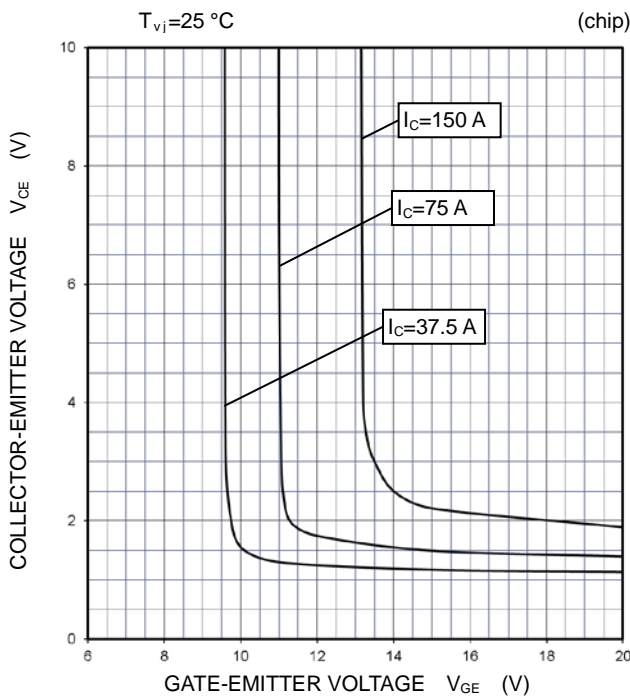
OUTPUT CHARACTERISTICS (TYPICAL)



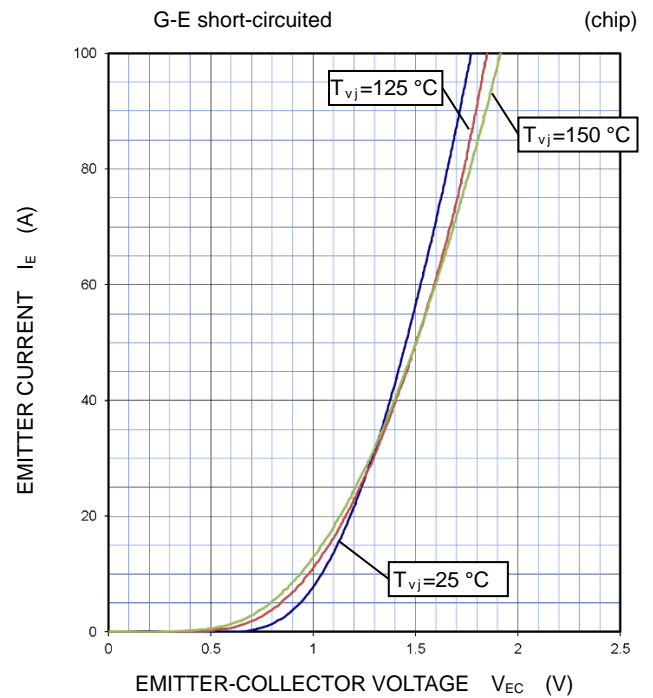
COLLECTOR-EMITTER SATURATION VOLTAGE CHARACTERISTICS (TYPICAL)



COLLECTOR-EMITTER VOLTAGE CHARACTERISTICS (TYPICAL)



DIODE FORWARD CHARACTERISTICS (TYPICAL)



CM100MXUD-13T1/CM100MXUDP-13T1

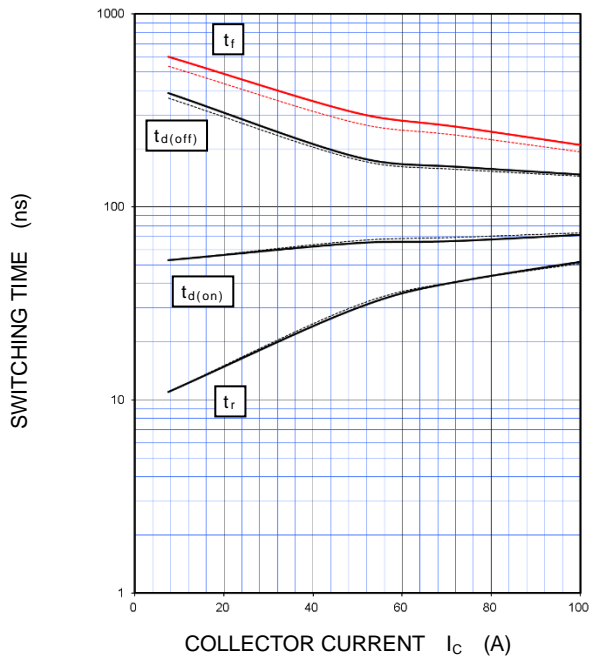
HIGH POWER SWITCHING USE
INSULATED TYPE

PERFORMANCE CURVES

BRAKE PART

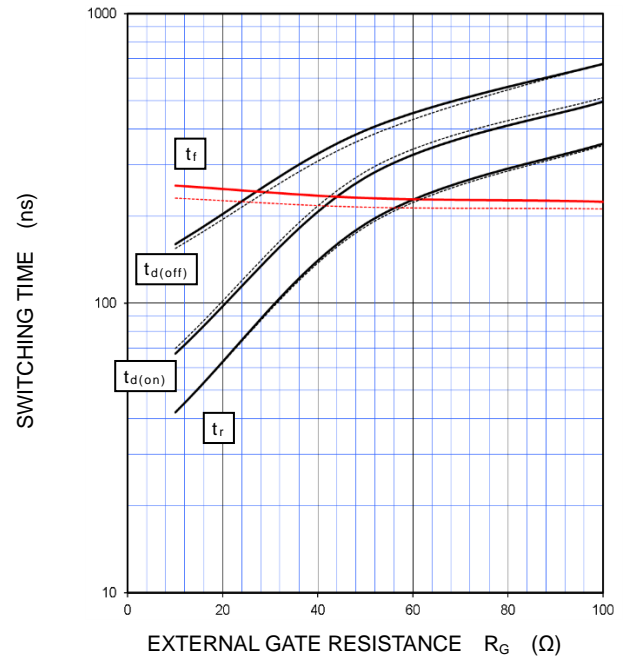
HALF-BRIDGE SWITCHING CHARACTERISTICS (TYPICAL)

$V_{CC}=300\text{ V}$, $R_G=10\ \Omega$, $V_{GE}=\pm 15\text{ V}$, INDUCTIVE LOAD
 —: $T_{vj}=150\text{ }^\circ\text{C}$, - - - -: $T_{vj}=125\text{ }^\circ\text{C}$



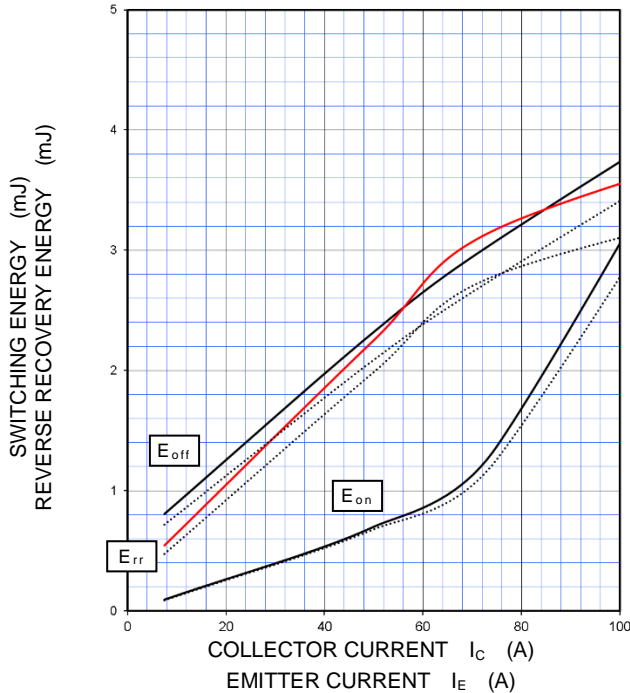
HALF-BRIDGE SWITCHING CHARACTERISTICS (TYPICAL)

$V_{CC}=300\text{ V}$, $I_c=75\text{ A}$, $V_{GE}=\pm 15\text{ V}$, INDUCTIVE LOAD
 —: $T_{vj}=150\text{ }^\circ\text{C}$, - - - -: $T_{vj}=125\text{ }^\circ\text{C}$



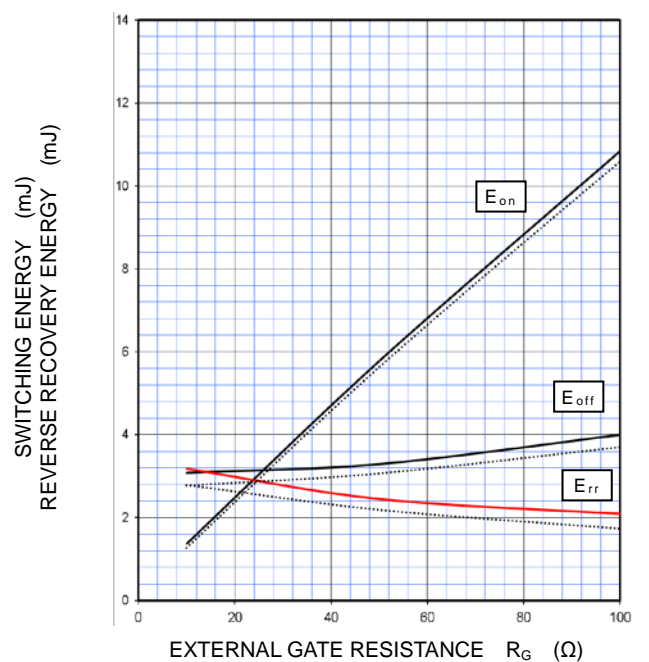
HALF-BRIDGE SWITCHING CHARACTERISTICS (TYPICAL)

$V_{CC}=300\text{ V}$, $R_G=10\ \Omega$, $V_{GE}=\pm 15\text{ V}$, INDUCTIVE LOAD,
 —: $T_{vj}=150\text{ }^\circ\text{C}$, - - - -: $T_{vj}=125\text{ }^\circ\text{C}$, PER PULSE



HALF-BRIDGE SWITCHING CHARACTERISTICS (TYPICAL)

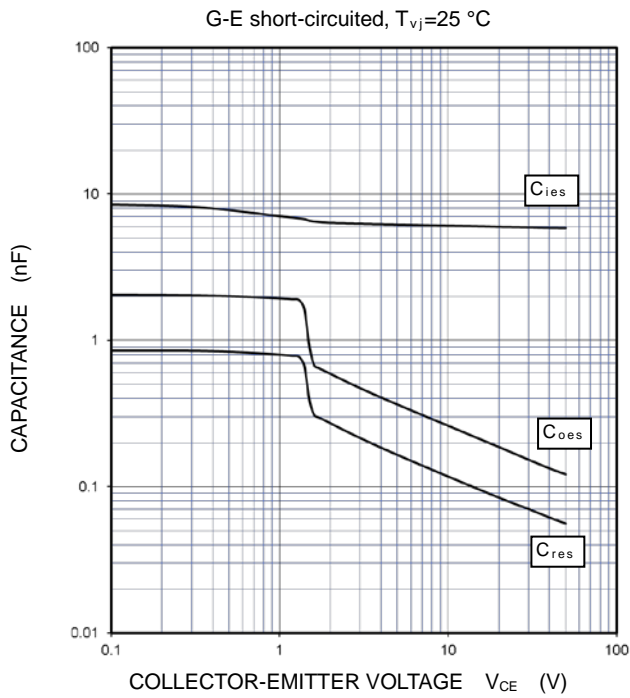
$V_{CC}=300\text{ V}$, $I_c/I_E=75\text{ A}$, $V_{GE}=\pm 15\text{ V}$, INDUCTIVE LOAD,
 —: $T_{vj}=150\text{ }^\circ\text{C}$, - - - -: $T_{vj}=125\text{ }^\circ\text{C}$, PER PULSE



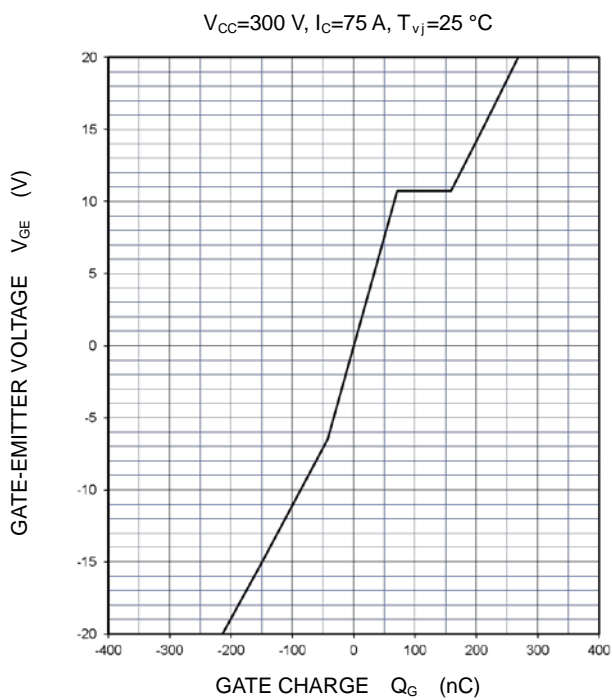
PERFORMANCE CURVES

BRAKE PART

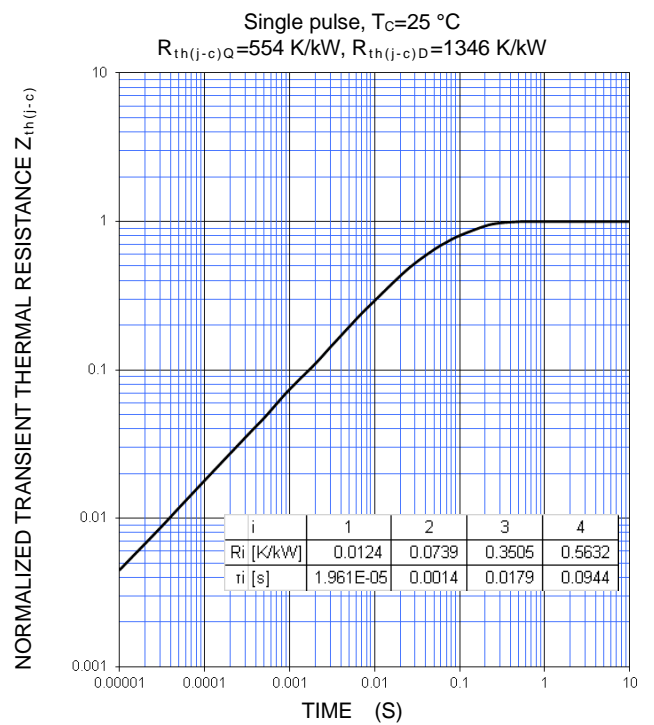
**CAPACITANCE CHARACTERISTICS
(TYPICAL)**



**GATE CHARGE CHARACTERISTICS
(TYPICAL)**



**TRANSIENT THERMAL IMPEDANCE CHARACTERISTICS
(MAXIMUM)**



CM100MXUD-13T1/CM100MXUDP-13T1

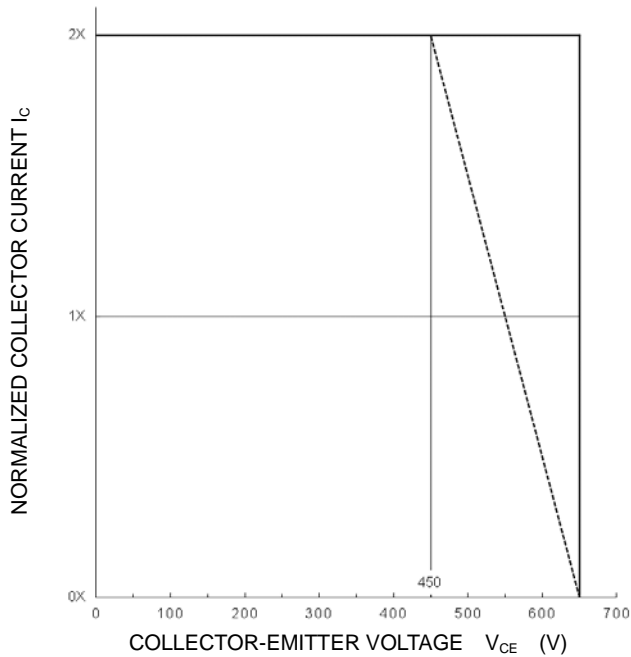
HIGH POWER SWITCHING USE
INSULATED TYPE

PERFORMANCE CURVES

BRAKE PART

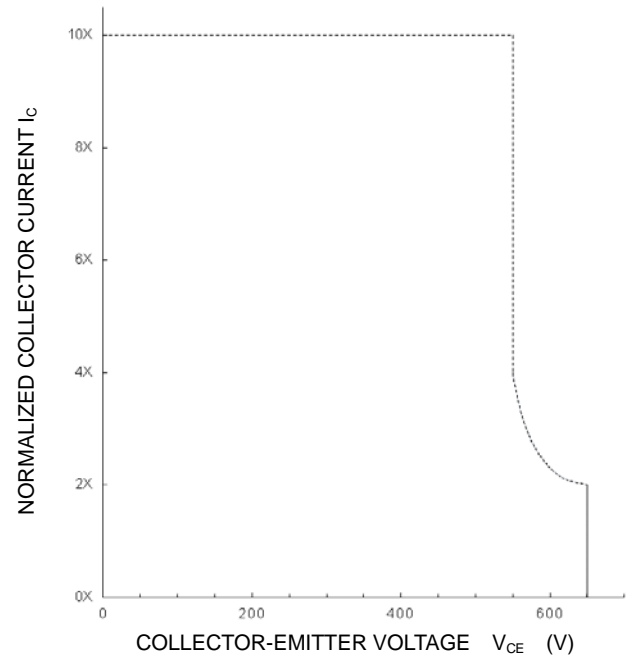
**TURN-OFF SWITCHING SAFE OPERATING AREA
(REVERSE BIAS SAFE OPERATING AREA)
(MAXIMUM)**

$V_{CC} \leq 450 \text{ V}$, $R_G = 10 \sim 100 \ \Omega$, $V_{GE} = \pm 15 \text{ V}$,
 ———: $T_{vj} = 25 \sim 150 \text{ }^\circ\text{C}$ (Normal load operations (Continuous))
 - - - - -: $T_{vj} = 175 \text{ }^\circ\text{C}$ (Unusual load operations (Limited period))



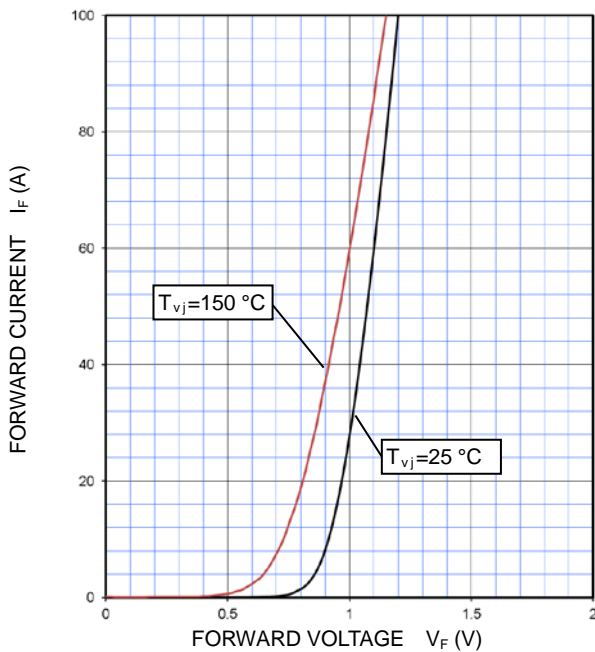
**SHORT-CIRCUIT SAFE OPERATING AREA
(MAXIMUM)**

$V_{CC} \leq 400 \text{ V}$, $R_G = 10 \sim 100 \ \Omega$, $V_{GE} = \pm 15 \text{ V}$,
 $T_{vj} = 25 \sim 150 \text{ }^\circ\text{C}$, $t_W \leq 8 \ \mu\text{s}$, Non-Repetitive



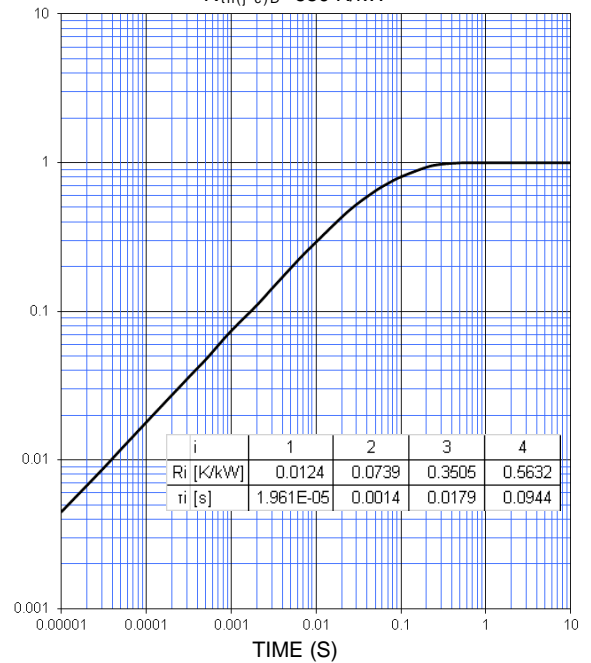
CONVERTER PART

**CONVERTER DIODE
FORWARD CHARACTERISTICS
(TYPICAL)**



**TRANSIENT THERMAL IMPEDANCE CHARACTERISTICS
(MAXIMUM)**

Single pulse, $T_C = 25 \text{ }^\circ\text{C}$
 $R_{th(j-c)D} = 650 \text{ K/kW}$



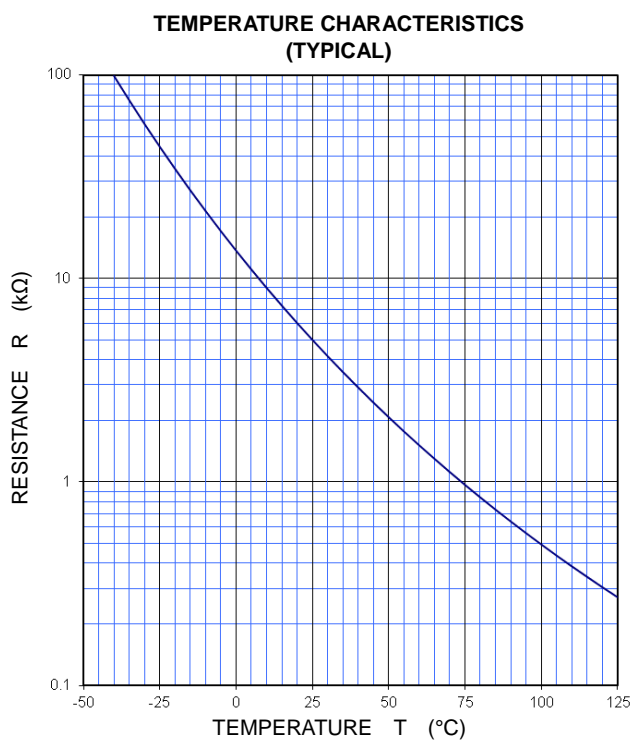
CM100MXUD-13T1/CM100MXUDP-13T1

HIGH POWER SWITCHING USE

INSULATED TYPE

PERFORMANCE CURVES

NTC thermistor part



Note: The characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

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